

ZXTN25020DFH

20V SOT23 NPN medium power transistor

Summary

$BV_{CEX} > 100V$; $BV_{(BR)CEO} > 20V$

$BV_{ECO} > 5V$;

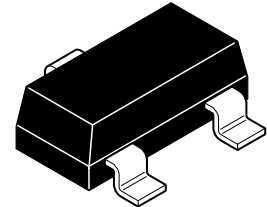
$I_{C(Cont)} = 4.5A$

$R_{CE(sat)} = 28\ m\Omega$ typical

$V_{CE(sat)} < 43\ mV$ @ 1A;

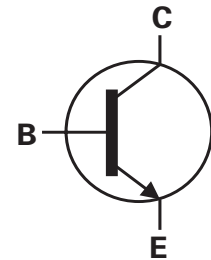
$P_D = 1.25W$

Complementary part number ZXTP25020DFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

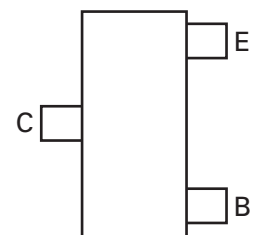


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 100V forward blocking voltage
- 5V reverse blocking voltage

Applications

- DC - DC converters
- MOSFET and IGBT gate driving
- LED driver
- Motor drive
- Relay, lamp and solenoid drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTN25020DFHTA	7	8mm	3000

Device marking

016

ZXTN25020DFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage (forward blocking)	V_{CEX}	100	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-collector voltage (reverse blocking)	V_{ECO}	5	V
Emitter-base voltage	V_{EBO}	7	V
Continuous collector current ^(c)	I_C	4.5	A
Base current	I_B	1	A
Peak pulse current	I_{CM}	15	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a)	P_D	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b)	P_D	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c)	P_D	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d)	P_D	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T_j, T_{stg}	- 55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	119	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	100	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

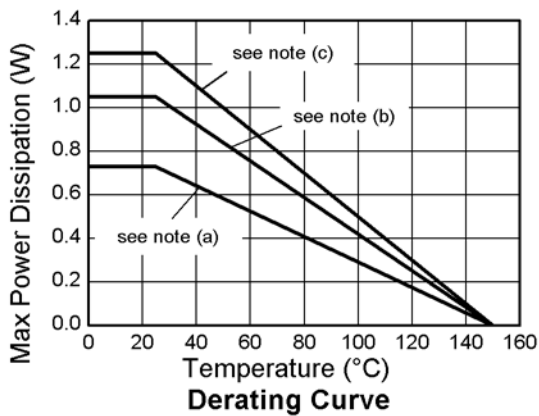
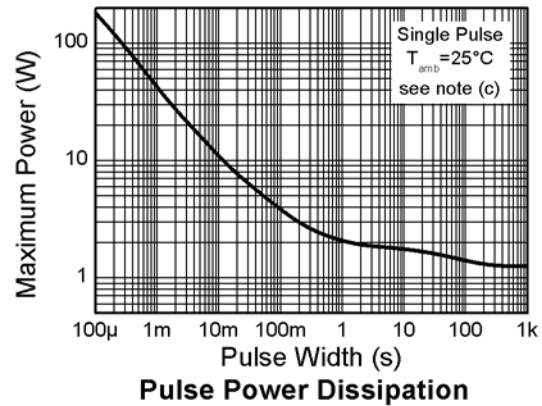
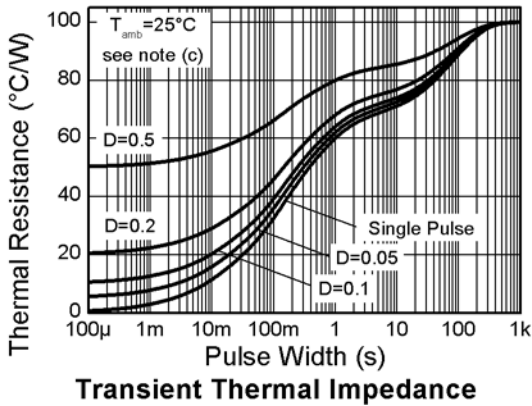
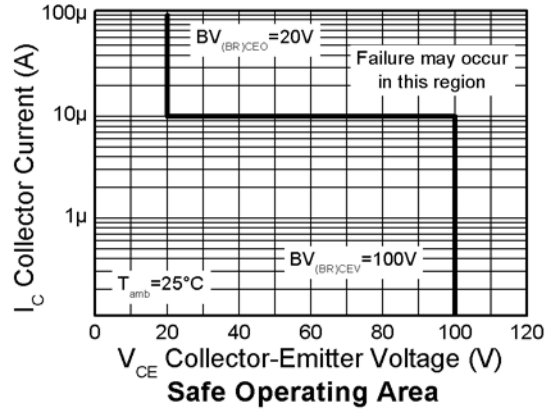
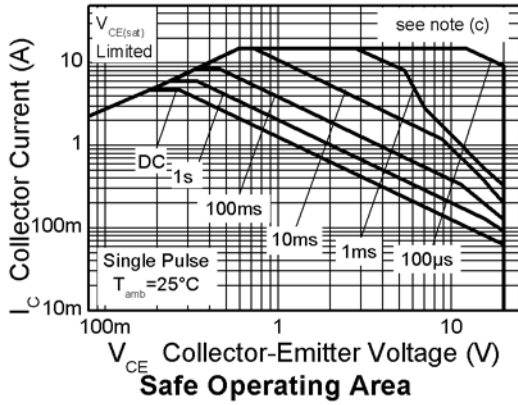
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at $t < 5\text{secs}$.

ZXTN25020DFH

Characteristics



ZXTN25020DFH

Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

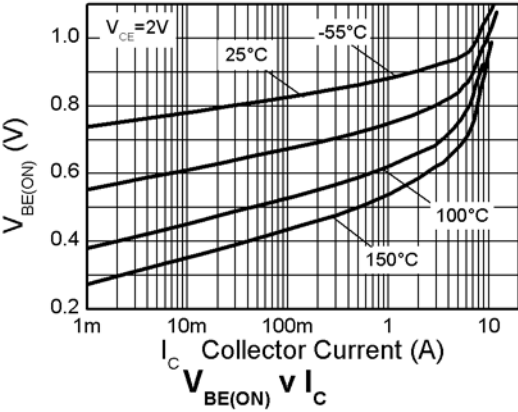
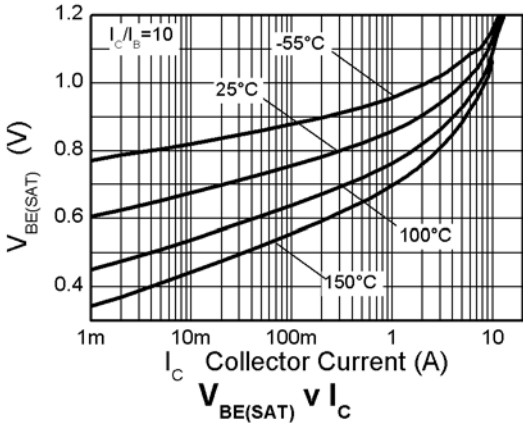
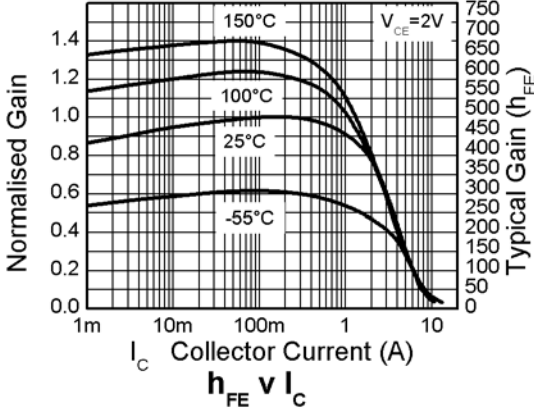
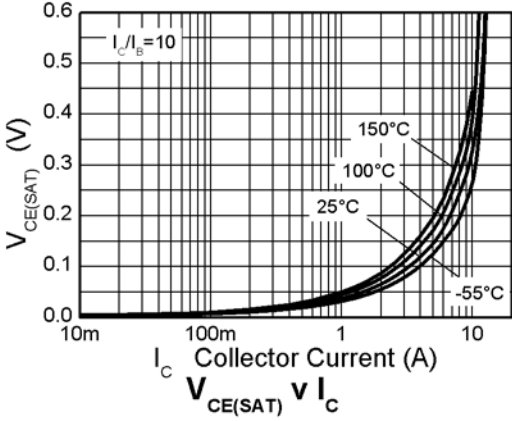
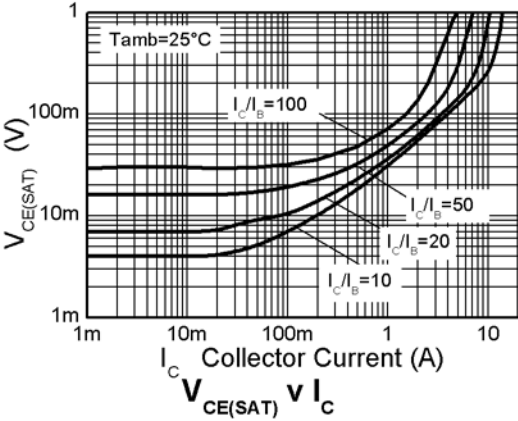
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector emitter breakdown voltage (base open)	BV_{CEO}	20	35		V	$I_C = 10\text{mA}^{(*)}$
Emitter-collector breakdown voltage (reverse blocking)	BV_{ECX}	6	8		V	$I_E = 100\mu\text{A}$, $R_{BC} \leq 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-collector breakdown voltage (base open)	BV_{ECO}	5	6		V	$I_E = 100\text{mA}$,
Emitter base breakdown voltage	BV_{EBO}	7	8.3		V	$I_E = 100\text{mA}$
Collector cut-off current	I_{CBO}		<1	50 20	nA μA	$V_{CB} = 100\text{V}$ $V_{CB} = 100\text{V}$, $T_{AMB} = 100^{\circ}\text{C}$
Collector emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = 100\text{V}$; $R_{BE} \leq 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$
Emitter cut-off current	I_{EBO}		<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector emitter saturation voltage	$V_{CE(sat)}$		35	43	mV	$I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$
			55	70	mV	$I_C = 1\text{A}$, $I_B = 20\text{mA}^{(*)}$
			90	110	mV	$I_C = 2\text{A}$, $I_B = 40\text{mA}^{(*)}$
			125	170	mV	$I_C = 2\text{A}$, $I_B = 20\text{mA}^{(*)}$
			125	150	mV	$I_C = 4.5\text{A}$, $I_B = 450\text{mA}^{(*)}$
			205	265	mV	$I_C = 4.5\text{A}$, $I_B = 90\text{mA}^{(*)}$
Base emitter saturation voltage	$V_{BE(sat)}$		900	1000	mV	$I_C = 4.5\text{A}$, $I_B = 90\text{mA}^{(*)}$
Base emitter turn-on voltage	$V_{BE(on)}$		820	900	mV	$I_C = 4.5\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	300	450	900		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$
		250	380			$I_C = 2\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
		120	170			$I_C = 4.5\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
		15				$I_C = 15\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	f_T		215		MHz	$I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	C_{OBO}		16.5	25	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	$t_{(d)}$		68		ns	$V_{CC} = 10\text{V}$. $I_C = 1\text{A}$, $I_{B1} = I_{B2} = 10\text{mA}$.
Rise time	$t_{(r)}$		72		ns	
Storage time	$t_{(s)}$		361		ns	
Fall time	$t_{(f)}$		64		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

ZXTN25020DFH

Characteristics



ZXTN25020DFH

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

For international sales offices visit www.zetex.com/offices

Zetex products are distributed worldwide. For details, see www.zetex.com/salesnetwork

This publication is issued to provide outline information only which (unless agreed by the company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contact or be regarded as a representation relating to the products or services concerned. The company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.



Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331